Rectifier diode

## FEATURES

- Extremely fast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET


## APPLICATIONS

- Active power factor correction
- Half-bridge lighting ballasts
- Half-bridge/ full-bridge switched mode power supplies.

The BYC10-600 is supplied in the SOD59 (TO220AC) conventional leaded package.

## SYMBOL



PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | cathode |
| 2 | anode |
| tab | cathode |
|  |  |

## QUICK REFERENCE DATA

| $\mathrm{V}_{\mathrm{R}}=600 \mathrm{~V}$ |
| :---: |
| $\mathrm{~V}_{\mathrm{F}} \leq 1.8 \mathrm{~V}$ |
| $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}=10 \mathrm{~A}$ |
| $\mathrm{t}_{\mathrm{rr}}=19 \mathrm{~ns}$ (typ) |

SOD59 (TO220AC)


## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {RRM }}$ | Peak repetitive reverse voltage |  |  | 600 | V |
| $\mathrm{V}_{\text {RWM }}$ | Crest working reverse voltage |  | - | 600 | V |
| $V_{\text {R }}$ | Continuous reverse voltage | $\mathrm{T}_{\mathrm{mb}} \leq 114{ }^{\circ} \mathrm{C}$ | - | 500 | V |
| $\mathrm{I}_{\text {f(AV) }}$ | Average forward current | $\delta=0.5$; with reapplied $\mathrm{V}_{\text {RRM(max) }}$; | - | 10 | A |
| $\mathrm{I}_{\text {FRM }}$ | Repetitive peak forward current | $\stackrel{\delta}{\mathrm{Sb}}=0.5$; with reapplied $\mathrm{V}_{\text {RRM (max) }}$; | - | 20 | A |
| $\mathrm{I}_{\text {FSM }}$ | Non-repetitive peak forward | $\mathrm{T}_{\mathrm{mb}} \leq 78$ $\mathrm{t}=10 \mathrm{~ms}$ | - | 65 | A |
|  | current. | $\mathrm{t}=8.3 \mathrm{~ms}$ <br> sinusoidal; $\mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$ prior to surge <br> with reapplied $\mathrm{V}_{\text {RWM(max) }}$ | - | 71 | A |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature Operating junction temperature |  | -40 | $\begin{aligned} & 150 \\ & 150 \end{aligned}$ | ${ }^{\circ} \mathrm{C}$ |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{th} \mathrm{j}-\mathrm{mb}}$ | Thermal resistance junction to <br> mounting base <br> $\mathrm{R}_{\mathrm{th} \mathrm{j}-\mathrm{a}}$ | Thermal resistance junction to <br> ambient | in free air. | - | - | 2 |
| $\mathrm{~K} / \mathrm{W}$ |  |  |  |  |  |  |

Rectifier diode ultrafast, low switching loss

## ELECTRICAL CHARACTERISTICS

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ unless otherwise stated

\begin{tabular}{|c|c|c|c|c|c|c|}
\hline SYMBOL \& PARAMETER \& CONDITIONS \& MIN. \& TYP. \& MAX. \& UNIT <br>
\hline $V_{F}$

$I_{R}$ \& | Forward voltage |
| :--- |
| Reverse current | \& \[

$$
\begin{aligned}
& I_{F}=10 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \\
& \mathrm{I}_{\mathrm{F}}=20 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \\
& \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \\
& \mathrm{V}_{\mathrm{R}}=600 \mathrm{~V} \\
& \mathrm{~V}_{\mathrm{R}}=500 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=100^{\circ} \mathrm{C} \\
& \hline
\end{aligned}
$$

\] \&  \& \[

$$
\begin{gathered}
1.4 \\
1.7 \\
2.0 \\
9 \\
1.1 \\
\hline
\end{gathered}
$$
\] \& 1.8

2.3
2.8
200

3.0 \& $$
\begin{gathered}
V \\
V \\
V \\
\mu A \\
\mathrm{~mA}
\end{gathered}
$$ <br>

\hline $$
\begin{aligned}
& \mathrm{t}_{\mathrm{r}} \\
& \mathrm{t}_{\mathrm{rr}} \\
& \mathrm{t}_{\mathrm{r}}
\end{aligned}
$$ \& Reverse recovery time Reverse recovery time Reverse recovery time \& \[

$$
\begin{aligned}
& \hline \mathrm{I}_{\mathrm{F}}=1 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=30 \mathrm{~V} ; \mathrm{dI}_{\mathrm{F}} / \mathrm{dt}=50 \mathrm{~A} / \mu \mathrm{s} \\
& \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=400 \mathrm{~V} ; \\
& \mathrm{d} \mathrm{l}_{\mathrm{F}} / \mathrm{dt}=500 \mathrm{~A} / \mu \mathrm{s} \\
& \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=400 \mathrm{~V} ; \\
& \mathrm{d} \mathrm{I}_{\mathrm{F}} / \mathrm{dt}=500 \mathrm{~A} / \mu \mathrm{s} ; \mathrm{T}_{\mathrm{j}}=125^{\circ} \mathrm{C} \\
& \hline
\end{aligned}
$$
\] \& -

- 
- \& $$
\begin{aligned}
& 35 \\
& 19 \\
& 32
\end{aligned}
$$ \& \[

$$
\begin{gathered}
55 \\
- \\
40
\end{gathered}
$$
\] \& ns ns ns <br>

\hline \[
$$
\begin{aligned}
& \mathrm{I}_{\mathrm{rrm}} \\
& \mathrm{I}_{\mathrm{rrm}}
\end{aligned}
$$

\] \& | Peak reverse recovery current |
| :--- |
| Peak reverse recovery current | \& \[

$$
\begin{aligned}
& \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{V}_{\mathrm{R}}=400 \mathrm{~V} ; \\
& \mathrm{dl}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} ; \mathrm{T}_{\mathrm{i}}=125^{\circ} \mathrm{C} \\
& \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{V}, 400 \mathrm{~V} ; \\
& \mathrm{d} \mathrm{I}_{\mathrm{F}} / \mathrm{dt}=500 \mathrm{~A} / \mu \mathrm{s} ; \mathrm{T}_{\mathrm{j}}=125^{\circ} \mathrm{C}
\end{aligned}
$$
\] \& - \& 3

9.5 \& 7.5
12 \& A
A <br>
\hline $\mathrm{V}_{\mathrm{fr}}$ \& Forward recovery voltage \& $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} ; \mathrm{dl}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s}$ \& - \& 8 \& 11 \& V <br>
\hline
\end{tabular}



Fig.1. Typical application, output rectifier in boost converter power factor correction circuit. Continuous conduction, mode where the transistor turns on whilst forward current is still flowing in the diode.


Fig.2. Typical application, freewheeling diode in half bridge converter. Continuous conduction mode, where each transistor turns on whilst forward current is still flowing in the other bridge leg diode.

Rectifier diode


Fig.3. Maximum forward dissipation as a function of average forward current; rectangular current waveform where $I_{F(A V)}=I_{F(R M S)} \times \sqrt{ } D$.


Fig.4. Typical reverse recovery switching losses in diode, as a function of rate of change of current $d_{F} / d t$.


Fig.5. Typical switching losses in transistor due to reverse recovery of diode, as a function of of change of current $d l_{F} / d t$.


Fig.6. Origin of switching losses in transistor due to diode reverse recovery.


Fig.7. Typical reverse recovery time $t_{r r}$, as a function of rate of change of current $d_{F} / d t$.


Fig.8. Typical peak reverse recovery current, $I_{\text {rrm }}$ as a function of rate of change of current $d I_{F} / d t$.

Rectifier diode


Fig.9. Definition of reverse recovery parameters $t_{r r}, I_{r r m}$


Fig.10. Typical forward recovery voltage, $V_{f r}$ as a function of rate of change of current $d l_{\digamma} / d t$.


Fig.11. Definition of forward recovery voltage $V_{t r}$


Fig.12. Typical and maximum forward characteristic $I_{F}=f\left(V_{F}\right) ; T_{j}=25^{\circ} \mathrm{C}$ and $150^{\circ} \mathrm{C}$.


Fig.13. Typical reverse leakage current as a function of reverse voltage. $I_{R}=f\left(V_{R}\right)$; parameter $T_{j}$


Fig.14. Maximum thermal impedance $Z_{\text {th } \dagger \text {-mb }}$ as a function of pulse width.

Rectifier diode
ultrafast, low switching loss

## MECHANICAL DATA



Fig.15. SOD59 (TO220AC). pin 1 connected to mounting base.

## Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

## Rectifier diode

## DEFINITIONS

| Data sheet status |  |
| :--- | :--- |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values |  |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one <br> or more of the limiting values may cause permanent damage to the device. These are stress ratings only and <br> operation of the device at these or at any other conditions above those given in the Characteristics sections of <br> this specification is not timplied. Exposure to limiting values for extended periods may affect device reliability. |  |
| Application information |  |
| Where application information is given, it is advisory and does not form part of the specification. |  |
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